

### 1. General description

High voltage, high speed, planar passivated NPN power switching transistor in a SOT54 (TO-92) plastic package.

### 2. Features and benefits

- Fast switching
- High typical DC current gain
- High voltage capability of 700 V
- Very low switching and conduction losses

### 3. Applications

- Compact fluorescent lamps (CFL)
- Low power electronic lighting ballasts
- Off-line self-oscillating power supplies (SOPS) for battery charging

### 4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>C</sub>	collector current	DC		-	-	1.5	А
P <sub>tot</sub>	total power dissipation	T <sub>lead</sub> ≤ 25 °C; <u>Fig. 1</u>		-	-	2.1	W
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V		-	-	700	V
Static characteristics							
h <sub>FE</sub>	DC current gain	$I_{C}$ = 0.5 A; $V_{CE}$ = 2 V; $T_{lead}$ = 25 °C		8	17	25	





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### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		Ç
2	С	collector		в-
3	E	emitter		E sym123
			TO-92 (SOT54)	5,in120

# 6. Ordering information

Table 3. Ordering information						
Type number Package						
	Name	Description	Version			
PHE13003C	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54			

### 7. Limiting values

#### Table 4.Limiting values

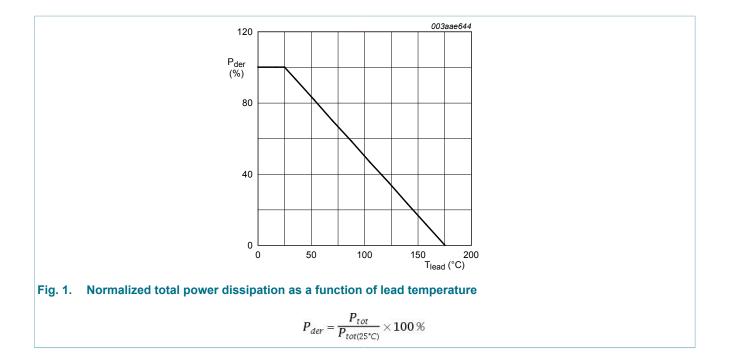
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V	-	700	V
V <sub>CBO</sub>	collector-base voltage	I <sub>E</sub> = 0 A	-	700	V
V <sub>CEO</sub>	collector-emitter voltage	I <sub>B</sub> = 0 A	-	400	V
I <sub>C</sub>	collector current	DC	-	1.5	А
I <sub>CM</sub>	peak collector current		-	3	А
I <sub>B</sub>	base current	DC	-	0.75	А
I <sub>BM</sub>	peak base current		-	1.5	А
P <sub>tot</sub>	total power dissipation	T <sub>lead</sub> ≤ 25 °C; <u>Fig. 1</u>	-	2.1	W
T <sub>stg</sub>	storage temperature		-65	150	°C
Tj	junction temperature		-	150	°C
V <sub>EBO</sub>	emitter-base voltage	I <sub>C</sub> = 0 A; I(Emitter) = 10 mA	-	9	V

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### 8. Thermal characteristics

#### Table 5. **Thermal characteristics** Conditions Symbol Parameter Min Max Unit Тур thermal resistance Fig. 2 60 K/W R<sub>th(j-lead)</sub> \_ \_ from junction to lead in free air; printed circuit board $\mathsf{R}_{\mathsf{th}(\mathsf{j-a})}$ thermal resistance 150 K/W -from junction to mounted; lead length = 4 mm ambient

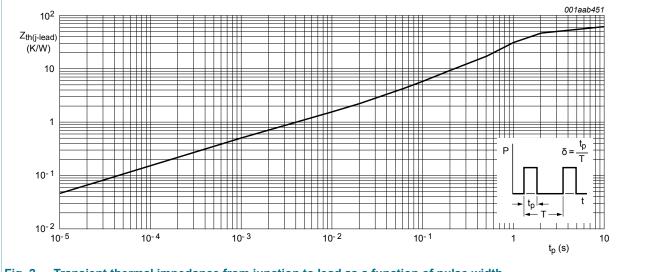


Fig. 2. Transient thermal impedance from junction to lead as a function of pulse width

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## 9. Characteristics

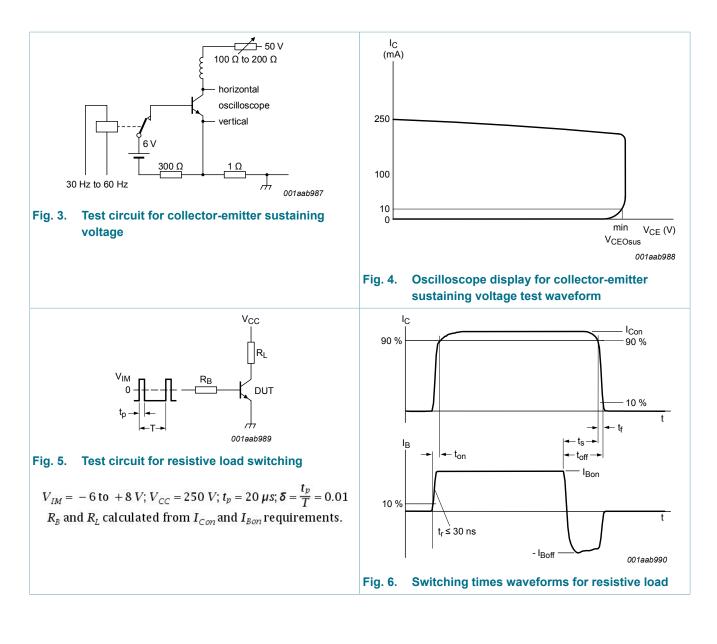
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic cl	naracteristics	· · · · · · · · · · · · · · · · · · ·				_
t <sub>on</sub>	turn-on time	I <sub>C</sub> = 1 A; I <sub>Bon</sub> = 0.2 A; I <sub>Boff</sub> = -0.2 A;	-	-	1	μs
t <sub>s</sub>	storage time	$R_L$ = 75 Ω; $T_{lead}$ = 25 °C; resistive load; Fig. 5; Fig. 6	-	-	4	μs
		$I_{C} = 1 \text{ A}; I_{Bon} = 0.2 \text{ A}; V_{BB} = -5 \text{ V};$ $L_{B} = 1 \mu\text{H}; T_{lead} = 25 \text{ °C}; \text{ inductive load};$ <u>Fig. 7; Fig. 8</u>	-	0.8	-	μs
t <sub>f</sub>	fall time	$I_C$ = 1 A; $I_{Bon}$ = 0.2 A; $I_{Boff}$ = -0.2 A; R <sub>L</sub> = 75 Ω; $T_{Iead}$ = 25 °C; resistive load; Fig. 5; Fig. 6	-	-	0.7	μs
		$I_{C}$ = 0.5 A; $I_{Bon}$ = 0.1 A; $V_{BB}$ = -5 V; $L_{B}$ = 1 µH; $T_{lead}$ = 25 °C; inductive load; Fig. 7; Fig. 8	-	0.1	-	μs
Static chara	acteristics	· · · · · · · · · · · · · · · · · · ·				
I <sub>CES</sub>		V <sub>BE</sub> = 0 V; V <sub>CE</sub> = 700 V; T <sub>j</sub> = 125 °C	-	-	5	mA
	current	$V_{BE}$ = 0 V; $V_{CE}$ = 700 V; $T_j$ = 25 °C	-	-	-	mA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE}$ = 400 V; I <sub>B</sub> = 0 A; T <sub>lead</sub> = 25 °C	-	-	0.1	mA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = 9 V; I <sub>C</sub> = 0 A; T <sub>lead</sub> = 25 °C	-	-	1	mA
V <sub>CEOsus</sub>	collector-emitter sustaining voltage	$I_B = 0 \text{ A}; I_C = 1 \text{ mA}; L_C = 25 \text{ mH};$ $T_{lead} = 25 \text{ °C}; Fig. 3; Fig. 4$	400	-	-	V
V <sub>CEsat</sub>	collector-emitter	I <sub>C</sub> = 0.5 A; I <sub>B</sub> = 0.1 A; T <sub>lead</sub> = 25 °C	-	-	0.5	V
	saturation voltage	$I_{C}$ = 1 A; $I_{B}$ = 0.25 A; $T_{lead}$ = 25 °C	-	-	1	V
		I <sub>C</sub> = 1.5 A; I <sub>B</sub> = 0.5 A; T <sub>lead</sub> = 25 °C	-	-	1.5	V
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{C}$ = 0.5 A; $I_{B}$ = 0.1 A; $T_{lead}$ = 25 °C	-	-	1	V
		$I_{C}$ = 1 A; $I_{B}$ = 0.25 A; $T_{lead}$ = 25 °C	-	-	1.2	V
h <sub>FE</sub>	DC current gain	$I_C$ = 0.5 A; $V_{CE}$ = 2 V; $T_{lead}$ = 25 °C	8	17	25	
		I <sub>C</sub> = 1 A; V <sub>CE</sub> = 2 V; T <sub>lead</sub> = 25 °C	5	9	15	

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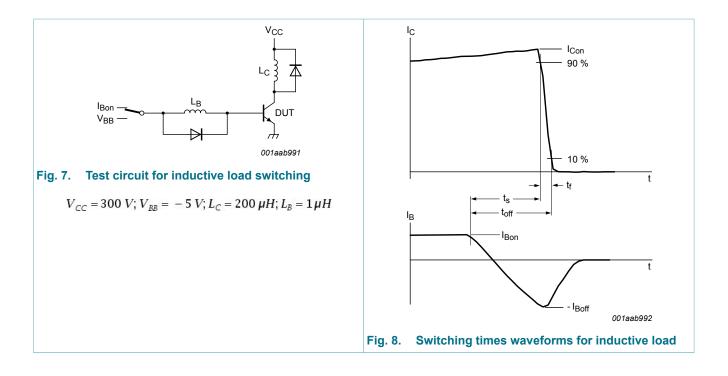
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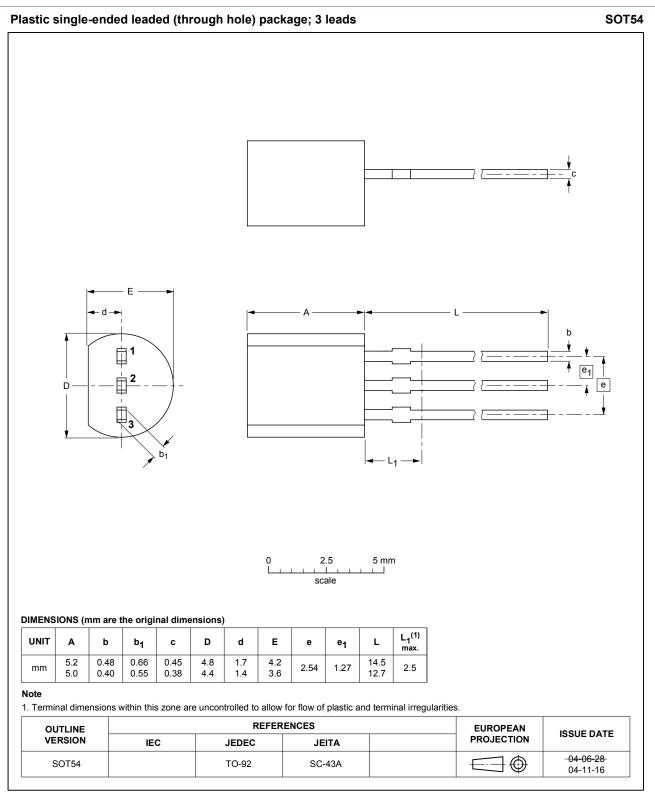
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### 10. Package outline



#### Fig. 9. Package outline TO-92 (SOT54)

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### 11. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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